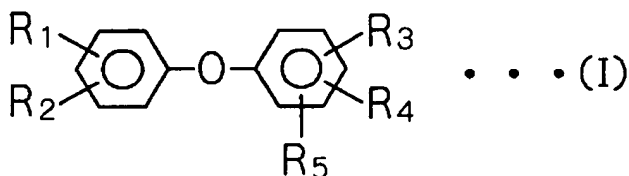


Appl. No. : Unknown  
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### AMENDMENTS TO THE CLAIMS

Please amend the Claims as indicated:

1. **(Original)** A developer composition for resists, comprising an organic quaternary ammonium base as a main component,  
said developer composition further comprising an anionic surfactant represented by the following general formula (I):



wherein at least one of R<sub>1</sub> and R<sub>2</sub> represents an alkyl or alkoxy group having 5 to 18 carbon atoms and the other one represents a hydrogen atom, or an alkyl or alkoxy group having 5 to 18 carbon atoms, and at least one of R<sub>3</sub>, R<sub>4</sub> and R<sub>5</sub> represents an ammonium sulfonate group or a sulfonic acid-substituted ammonium group and the others represent a hydrogen atom, an ammonium sulfonate group or a sulfonic acid-substituted ammonium group, and SO<sub>4</sub><sup>2-</sup>, the content being from 10 to 10,000 ppm.

2. **(Original)** The developer composition for resists according to claim 1, further comprising a lower alcohol, the content being from 0.01 to 5% by mass.

3. **(Original)** The developer composition for resists according to claim 1, further comprising a halogen ion, the content being 1000 ppm or less.

4. **(Currently amended)** A method for formation of a resist pattern, comprising applying a resist composition on a substrate to form a resist layer, prebaking the resist layer, selectively exposing the prebaked resist layer to light, and alkali-developing the exposed resist layer with the developer composition for resists according to claim 1 ~~any one of claims 1 to 3~~ to form a resist pattern.